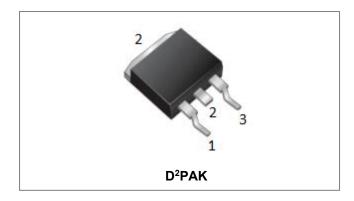






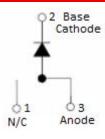
### **SDURB860 ULTRAFAST RECTIFIER**



#### **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### **Circuit Diagram**



#### **Features**

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- "-A" is an AEC-Q101 qualified device
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	600	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=100°C, rectangular wave form	8	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	110	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 8A, Pulse, T <sub>J</sub> = 25°C	1.35	1.7	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	0.2	8	μA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125^{\circ}C$	0.15	1	mA
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =500mA, I <sub>R</sub> =1A,and I <sub>m</sub> =250mA	45	50	ns

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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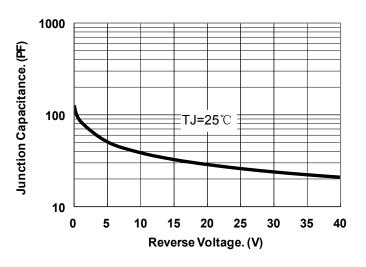




### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	R <sub>0</sub> JA	DC operation	25	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D <sup>2</sup> PAK			

## **Ratings and Characteristics Curves**



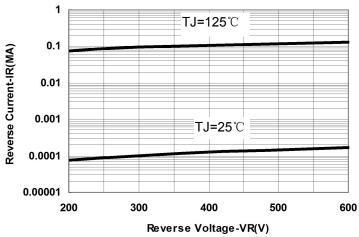


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

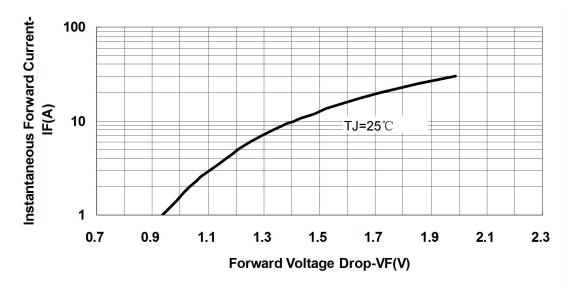


Fig.3-Typical Forward Voltage Drop Characteristics

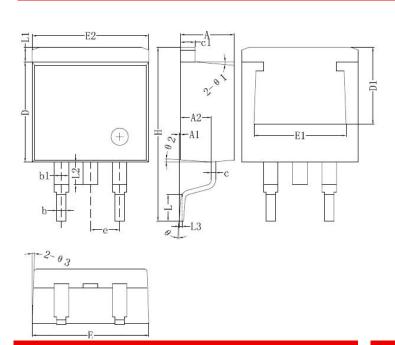
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#### Mechanical Dimensions D<sup>2</sup>PAK



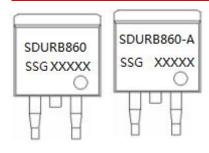
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
Α	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
С	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
е		2.54	
Н	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
е	0	-	8°
e1		5°	
e2		4°	
e3		4°	

### **Ordering Information**

Device	Package	Shipping
SDURB860	D <sup>2</sup> PAK	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

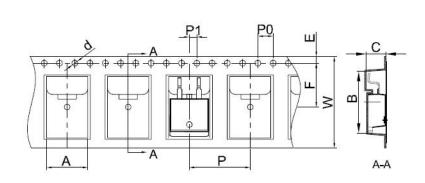
SDUR = Device Type
B = Package type
8 = Forward Current (8A)
60 = Reverse Voltage(600V)

-A = AEC-Q101 SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

# Carrier Tape Specification D<sup>2</sup>PAK



CVMPOL	Millimeters		
SYMBOL	Min.	Max.	
Α	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

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